

Brac University**Set: 01**

Semester: Summer 2023

Course No: CSE251

Course Title: Electronic Devices and Circuits

Section: 1 to 10

Final Exam

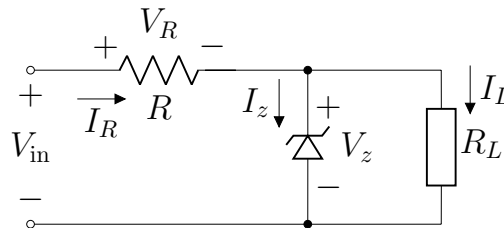
Full Marks: 30

Time: 1 hour 30 minutes

Date: 03 September, 2023

Answer **any 3 out of 4** questions. All the questions carry equal marks.**Question 1 [CO3]****10**

A Zener diode voltage regulator has a regulation voltage of 5.1 V when the current through the Zener diode is 50 mA. It is characterized by the parameters, $r_z = 5 \Omega$, $I_{ZK} = 5 \text{ mA}$.

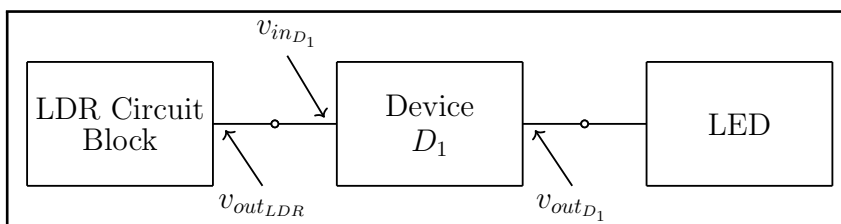


- Determine** the cut-in voltage, V_{Z0} of the zener diode. [1.5]
- Assume, the nominal value of the supply voltage, V_{in} is 15 V and $R = 200 \Omega$. **Calculate** I_R , R_L and I_L for the worst case scenario. [1+1+1]
- Now, assume, R_L and R are both 100Ω each. **Calculate** the minimum value of the supply voltage V_{in} at the worst case scenario. [3]
- The supply voltage of the regulator is now given as $15 \pm 1 \text{ V}$. **Design** the voltage regulator circuit, i.e., **determine the value of R** , such that even in the worst-case scenario, voltage regulation is maintained and the circuit sustains a load current of 8 mA. [2.5]

Bonus: Analyze the effect of decreasing the load resistance, R_L and **explain** briefly. [2]

Question 2 [CO1]**10**

Rosa has a switching device, **D₁** built with **2 MOSFETs**. The MOSFETs have the following parameters, $k = 1 \text{ mA/V}^2$ and $V_T = 0.2 \text{ V}$. The device turns ON an LED light in her dollhouse at night and turns the light OFF during the day. The supply voltage of the device is, $V_{SS} = 10 \text{ V}$ and the load resistance is $R_L = 10 \text{ k}\Omega$. The input voltage of the device, v_{inD1} is taken from the output voltage of an LDR Circuit Block, v_{outLDR} as shown in the diagram below. Rosa measured the voltages and made the following table where, **HIGH** $\equiv 5 \text{ V}$ and **LOW** $\equiv 1.5 \text{ V}$.



Time	v_{outLDR}	v_{inD1}	v_{outD1}
Day	LOW	LOW	LOW
Night	HIGH	HIGH	HIGH

- Identify** and **explain** the logical operation of the switching device, D_1 . [1+1]
- Draw** the circuit diagram of the device, D_1 with proper labeling. [2]
- Calculate** the on-state resistance, R_{ON} of the 1st MOSFET of the device. [2]
- Draw** the Voltage Transfer Characteristic (VTC) of the device with proper labeling. [2+2]

Bonus: Determine the W/L sizing of the 1st MOSFET. [2]

Equations for MOSFET

Cut-off: $I_D = 0$, if $V_{GS} < V_T$

Triode: $I_D = k \left[(V_{GS} - V_T) V_{DS} - \frac{1}{2} V_{DS}^2 \right]$, if $V_{GS} \geq V_T$ and $V_{DS} < (V_{GS} - V_T)$

Saturation: $I_D = \frac{1}{2} k (V_{GS} - V_T)^2$, if $V_{GS} \geq V_T$ and $V_{DS} \geq (V_{GS} - V_T)$

Question 3 [CO3]

10

Answer the following questions for **Figure-1** where $R_1 = 1k\Omega$, $R_2 = 2k\Omega$, $R_3 = 3k\Omega$, $R_4 = 4k\Omega$.

- Why a MOSFET can be used as a switch? **Explain** briefly. [2]
- Analyze** the circuit in *Figure-1* to **determine** the values of I_C , I_B , I_E , v_C of T_1 . [3]
- Analyze** the circuit in *Figure-1* to **determine** the value of I_{DS2} , v_O of T_2 . [5]

Bonus: **Design** a circuit with the boolean inputs A, B, C, D using ideal MOSFETs (S-model) to implement the logic function, $f = \overline{A.C} + B.D$ [2]

Question 4 [CO1, CO3]

10

- Draw** the I-V characteristic of a BJT. **Indicate** the operating regions with proper labeling. [2]
- A linear amplifier follows the equation, $V_{out} = -5V_{in}$ where the valid input range is -10V to +10V. **Illustrate** the Voltage Transfer Characteristic (VTC) of the amplifier with proper labels. [2]
- For the BJT CE Amplifier of **Figure-2**, $v_{IN} = 2 + 0.2 \sin(100\pi t)$ and $v_O = 4 - 2 \sin(100\pi t)$. **Design** the Amplifier circuit, i.e., **calculate** the value of V_S , R_L and R_i . [2+2+2]

Bonus: **Identify** the lowest value of the input voltage for which amplification occurs. **Explain** your reasoning. [2]

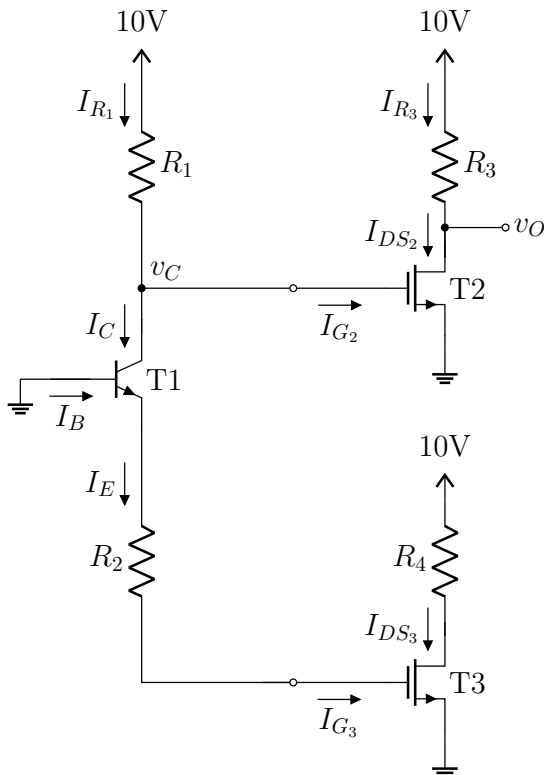


Figure-1

for BJT

$\beta = 100$
 $\alpha = 0.99$
 $v_{BE(Active)} = 0.7V$
 $v_{BE(Saturation)} = 0.8V$
 $v_{CE(Saturation)} = 0.2V$

for MOSFET

$V_T = 1V$
 $k = 5mA/V^2$

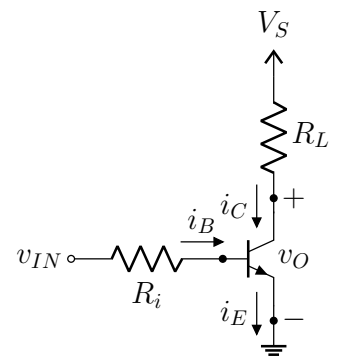


Figure-2